

MMBT4401M3T5G

NPN Switching Transistor

The MMBT4401M3T5G device is a spin-off of our popular SOT-23 three-leaded device. It is designed for general purpose switching applications and is housed in the SOT-723 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

Features

- Reduces Board Space
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	40	Vdc
Collector – Base Voltage	V_{CBO}	60	Vdc
Emitter – Base Voltage	V_{EBO}	6.0	Vdc
Collector Current – Continuous	I_C	600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	265	mW
		2.1	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	470	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	640	mW
		5.1	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	195	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

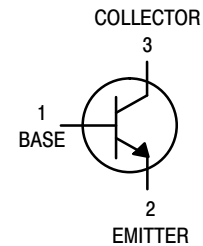
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

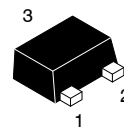


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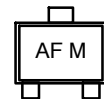
<http://onsemi.com>



MARKING DIAGRAM



SOT-723
CASE 631AA
STYLE 1



AF = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
MMBT4401M3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBT4401M3T5G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector - Emitter Breakdown Voltage (Note 3) ($I_C = 1.0 \text{ mA dc}$, $I_B = 0$)	$V_{(BR)CEO}$	40	-	Vdc
Collector - Base Breakdown Voltage ($I_C = 0.1 \text{ mA dc}$, $I_E = 0$)	$V_{(BR)CBO}$	60	-	Vdc
Emitter - Base Breakdown Voltage ($I_E = 0.1 \text{ mA dc}$, $I_C = 0$)	$V_{(BR)EBO}$	6.0	-	Vdc
Base Cutoff Current ($V_{CE} = 35 \text{ Vdc}$, $V_{EB} = 0.4 \text{ Vdc}$)	I_{BEV}	-	0.1	$\mu\text{A dc}$
Collector Cutoff Current ($V_{CE} = 35 \text{ Vdc}$, $V_{EB} = 0.4 \text{ Vdc}$)	I_{CEX}	-	0.1	$\mu\text{A dc}$

ON CHARACTERISTICS (Note 3)

DC Current Gain ($I_C = 0.1 \text{ mA dc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 1.0 \text{ mA dc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 10 \text{ mA dc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 150 \text{ mA dc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 500 \text{ mA dc}$, $V_{CE} = 2.0 \text{ Vdc}$)	h_{FE}	20 40 80 100 40	- - - 300 -	-
Collector - Emitter Saturation Voltage ($I_C = 150 \text{ mA dc}$, $I_B = 15 \text{ mA dc}$) ($I_C = 500 \text{ mA dc}$, $I_B = 50 \text{ mA dc}$)	$V_{CE(sat)}$	- -	0.4 0.75	Vdc
Base - Emitter Saturation Voltage ($I_C = 150 \text{ mA dc}$, $I_B = 15 \text{ mA dc}$) ($I_C = 500 \text{ mA dc}$, $I_B = 50 \text{ mA dc}$)	$V_{BE(sat)}$	0.75 -	0.95 1.2	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current - Gain - Bandwidth Product ($I_C = 20 \text{ mA dc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	250	-	MHz
Collector - Base Capacitance ($V_{CB} = 5.0 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{cb}	-	6.5	pF
Emitter - Base Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_C = 0$, $f = 1.0 \text{ MHz}$)	C_{eb}	-	30	pF
Input Impedance ($I_C = 1.0 \text{ mA dc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{ie}	1.0	15	$k\Omega$
Voltage Feedback Ratio ($I_C = 1.0 \text{ mA dc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{re}	0.1	8.0	$\times 10^{-4}$
Small - Signal Current Gain ($I_C = 1.0 \text{ mA dc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{fe}	40	500	-
Output Admittance ($I_C = 1.0 \text{ mA dc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{oe}	1.0	30	μmhos

SWITCHING CHARACTERISTICS

Delay Time	($V_{CC} = 30 \text{ Vdc}$, $V_{EB} = 2.0 \text{ Vdc}$, $I_C = 150 \text{ mA dc}$, $I_{B1} = 15 \text{ mA dc}$)	t_d	-	15	ns
Rise Time		t_r	-	20	
Storage Time	($V_{CC} = 30 \text{ Vdc}$, $I_C = 150 \text{ mA dc}$, $I_{B1} = I_{B2} = 15 \text{ mA dc}$)	t_s	-	225	ns
Fall Time		t_f	-	30	

3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

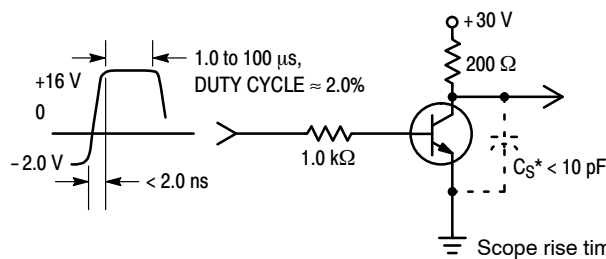


Figure 1. Turn-On Time

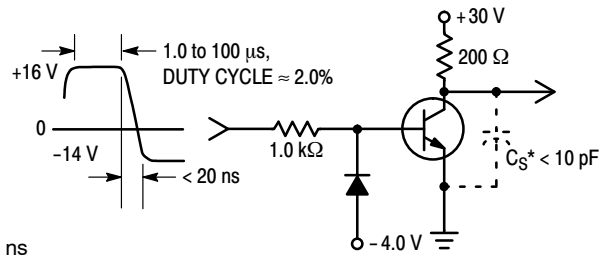


Figure 2. Turn-Off Time

MMBT4401M3T5G

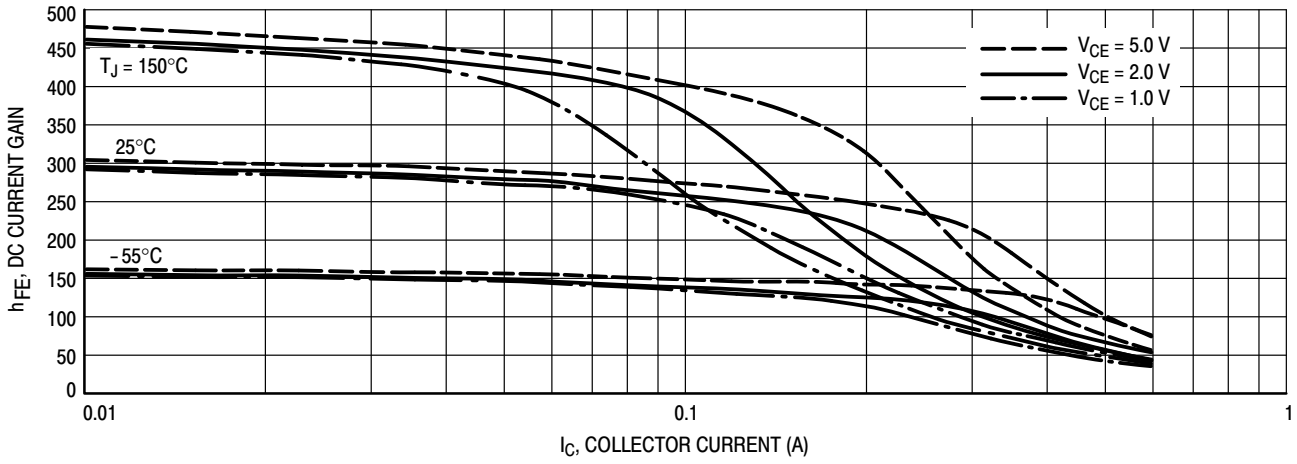


Figure 3. DC Current Gain

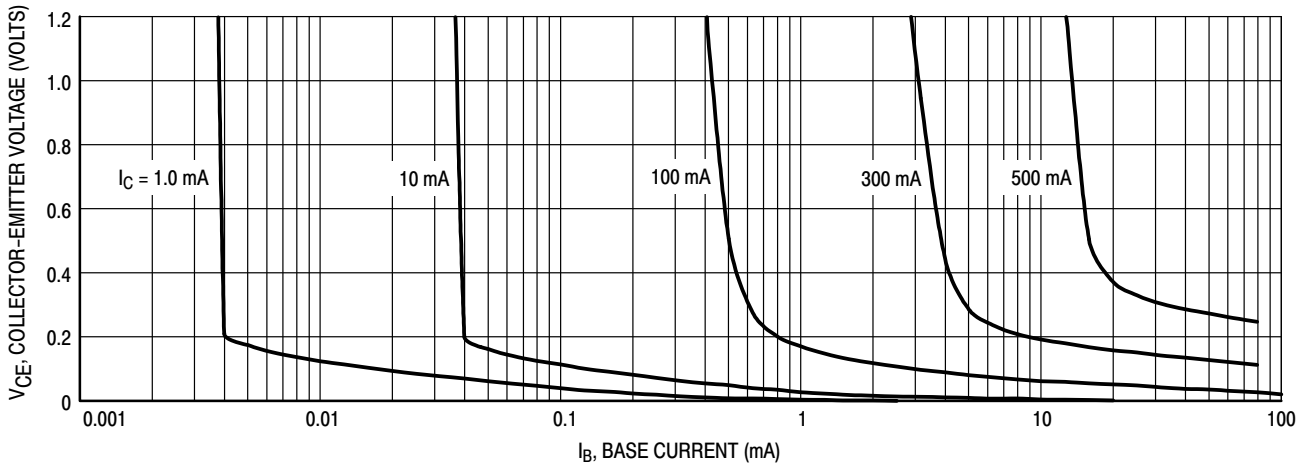


Figure 4. Collector Saturation Region

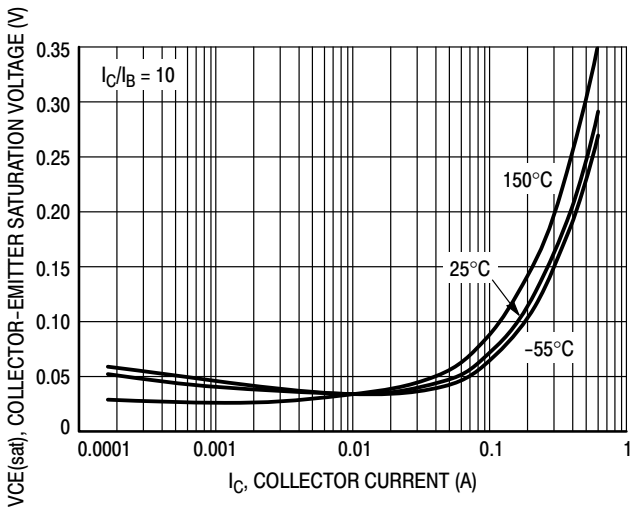


Figure 5. Collector-Emitter Saturation Voltage vs. Collector Current

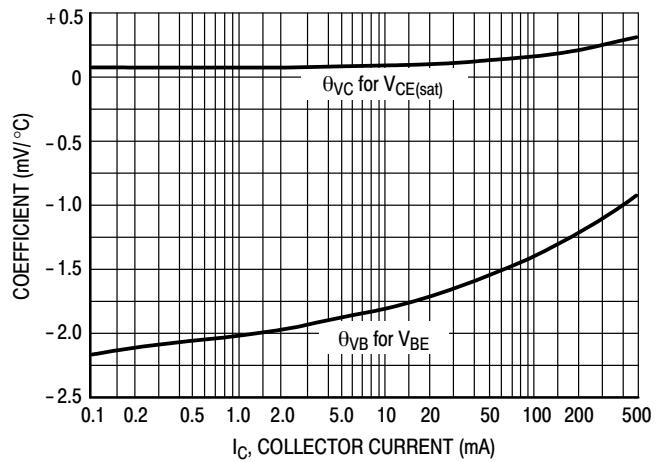


Figure 6. Temperature Coefficients

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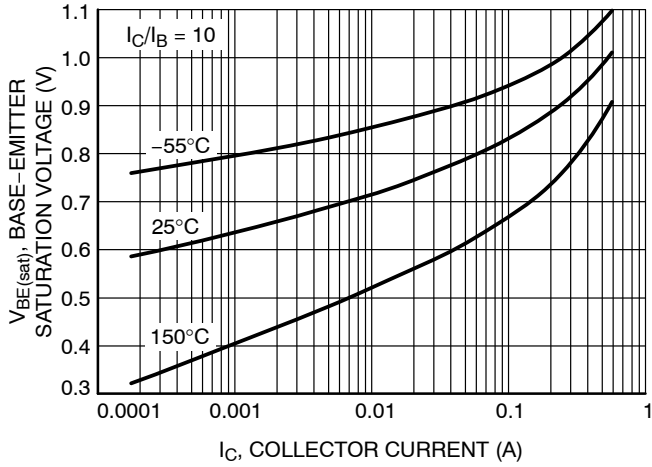


Figure 7. Base-Emitter Saturation Voltage vs. Collector Current

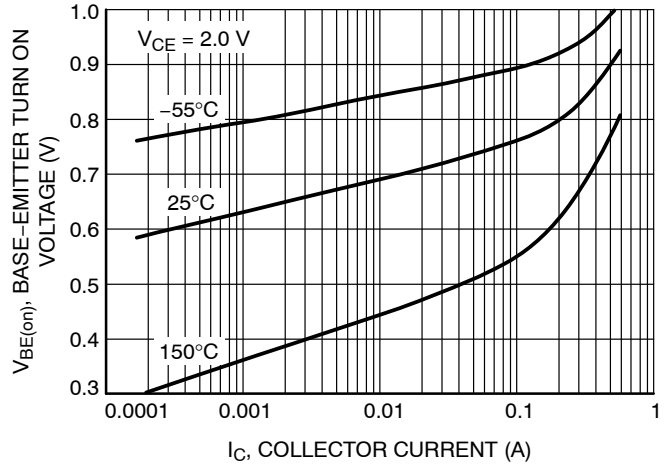


Figure 8. Base-Emitter Turn On Voltage vs. Collector Current

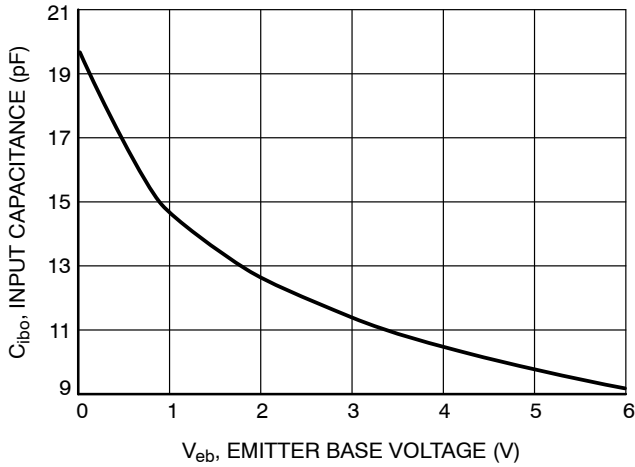


Figure 9. Input Capacitance vs. Emitter Base Voltage

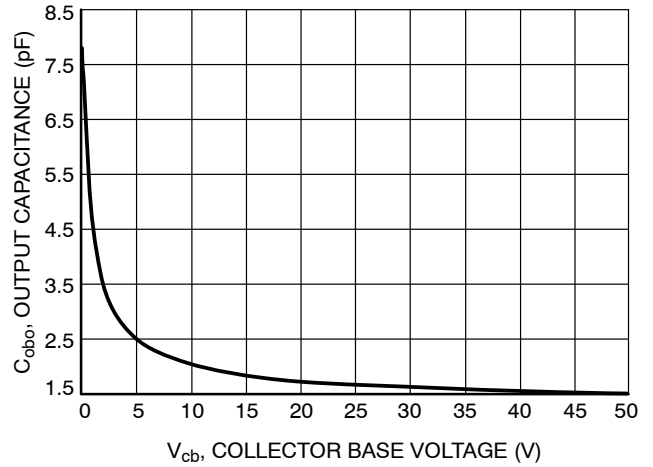


Figure 10. Output Capacitance vs. Collector Base Voltage

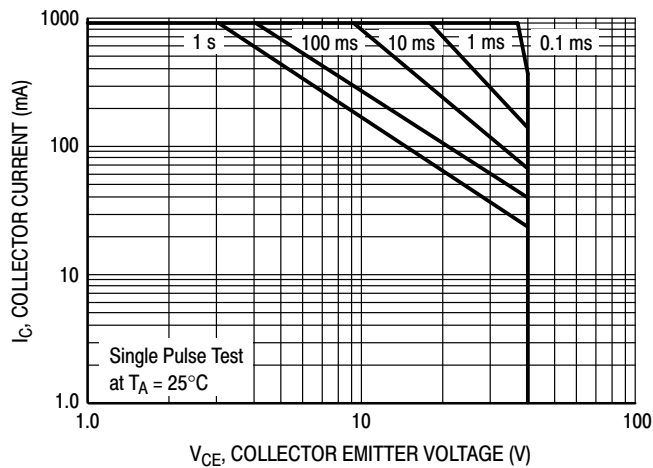


Figure 11. Safe Operating Area

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

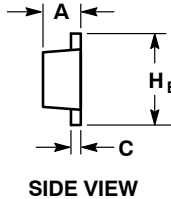
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SCALE 4:1

SOT-723
CASE 631AA-01
ISSUE D

DATE 10 AUG 2009

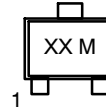


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

- | | | | | |
|-------------------------------------------------------|--------------------------------------------------|----------------------------------------------------|------------------------------------------------------|--------------------------------------------------|
| STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE | STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE | STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN |
|-------------------------------------------------------|--------------------------------------------------|----------------------------------------------------|------------------------------------------------------|--------------------------------------------------|

RECOMMENDED SOLDERING FOOTPRINT*



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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